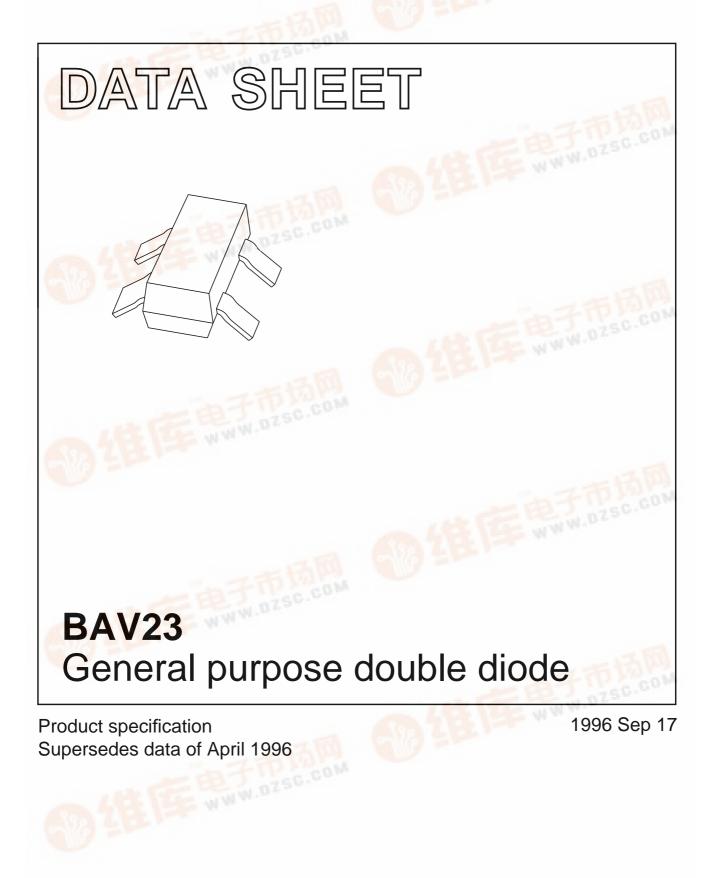
DISCRETE SEMICONDUCTORS









1996 Sep 17

General purpose double diode

FEATURES

- Small plastic SMD package
- Switching speed: max. 50 ns
- General application
- Continuous reverse voltage: max. 200 V
- Repetitive peak reverse voltage: max. 250 V
- Repetitive peak forward current: max. 625 mA.

APPLICATIONS

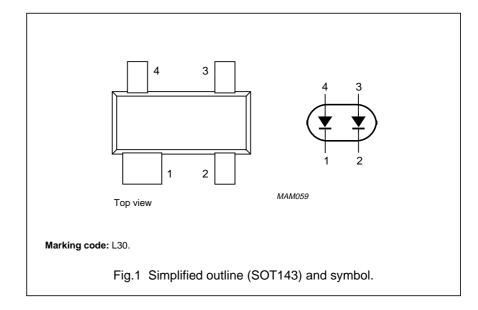
General purpose where high
breakdown voltages are required.

DESCRIPTION

The BAV23 consists of two general purpose diodes fabricated in planar technology, and encapsulated in the small plastic SMD SOT143 package. The diodes are not connected.

PINNING

PIN	DESCRIPTION
1	cathode (k1)
2	cathode (k2)
3	anode (a2)
4	anode (a1)



Product specification

BAV23

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage		_	250	V
V _{RRM}	repetitive peak reverse voltage	series connection		500	V
V _R	continuous reverse voltage		-	200	V
V _R	continuous reverse voltage	series connection	-	400	V
I _F	continuous forward current	single diode loaded; see Fig.2; note 1	_	225	mA
		double diode loaded; see Fig.2; note 1	_	125	mA
I _{FRM}	repetitive peak forward current		-	625	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	9	A
		t = 100 μs	-	3	A
		t = 10 ms	_	1.7	A
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	-	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

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ELECTRICAL CHARACTERISTICS

 $T_j = 25 \ ^{\circ}C$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _F	forward voltage	see Fig.3			
		I _F = 100 mA	_	1.0	V
		I _F = 200 mA	-	1.25	V
V _F	forward voltage	series connection; see Fig.3			
		I _F = 100 mA	-	2.0	V
		I _F = 200 mA	_	2.5	V
I _R	reverse current	see Fig.5			
		V _R = 200 V	-	100	nA
		$V_{R} = 200 \text{ V}; \text{ T}_{j} = 150 ^{\circ}\text{C}$	_	100	μA
I _R	reverse current	series connection	-		
		V _R = 400 V	-	100	nA
		V _R = 400 V; T _j = 150 °C	-	100	μA
C _d	diode capacitance	$f = 1 \text{ MHz}; V_R = 0; \text{ see Fig.6}$	_	5	pF
		series connection; f = 1 MHz; V_R = 0; see Fig.6	_	2.5	pF
t _{rr}	reverse recovery time		_	50	ns

THERMAL CHARACTERISTICS

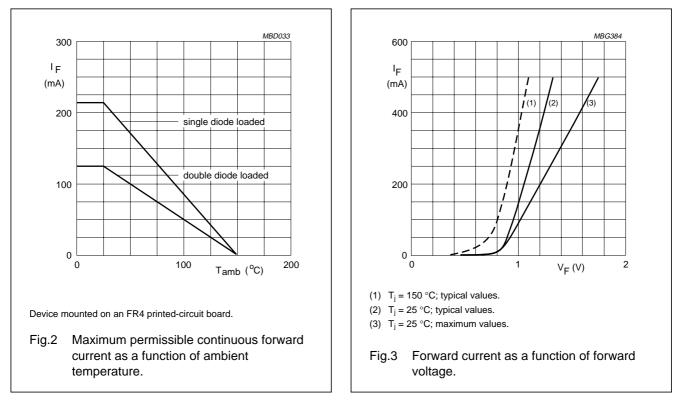
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point		360	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

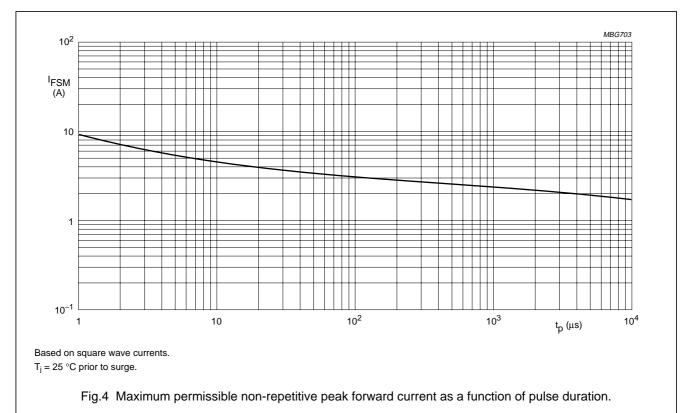
Note

1. Device mounted on an FR4 printed-circuit board.

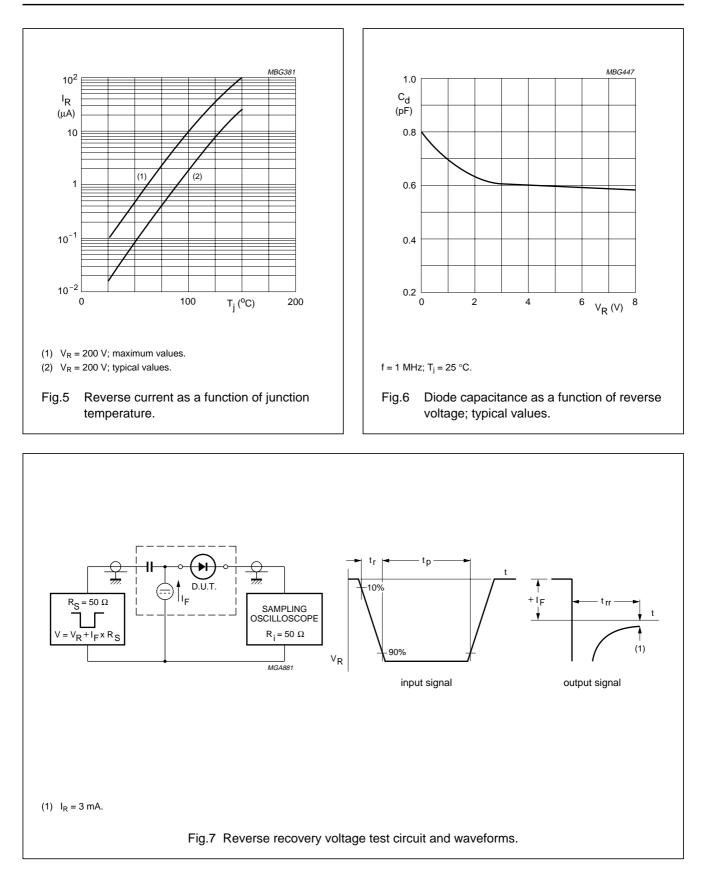
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GRAPHICAL DATA



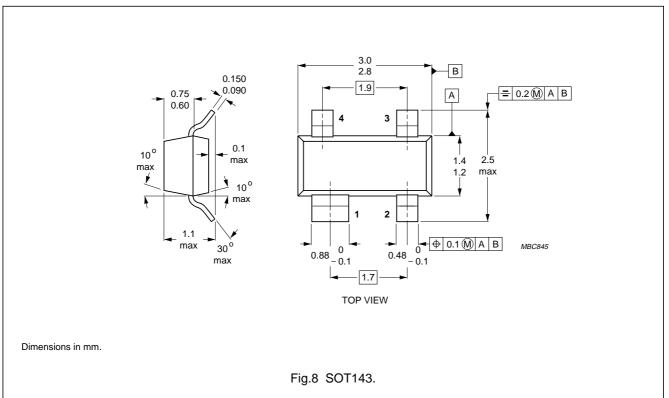


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PACKAGE OUTLINE



DEFINITIONS

Data Sheet Status		
Objective specification	This data sheet contains target or goal specifications for product development.	
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.	
Product specification	This data sheet contains final product specifications.	
Limiting values		
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.		
Application information		
Where application information is given, it is advisory and does not form part of the specification.		

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.